

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	15335	(scan\$4 near2 (probe or tunnel\$4) near2 microscope) or (spm or stm)	US-PGPUB; USPAT	OR	ON	2007/02/21 07:38
L2	12982	(atomic near2 force near2 microscope) or afm	US-PGPUB; USPAT	OR	ON	2007/02/21 07:38
L3	23787	resistiv\$5 near2 layer	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/21 07:39
L4	33150	(control\$4 or vary\$4 or variable or chang\$4 or first or second or plural\$4 or multiple or different) near2 resistiv\$5	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/21 07:39
L5	4	L3 same L4 same (L1 or L2)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/21 07:39
L6	45540	(carbon or (carbon near2 resistiv\$5)) near2 (layer or element)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/21 07:41
L7	2822498	voltage or current	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/21 07:41
L8	81078	active near2 layer	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/21 07:41
L9	31113	(control\$4 or vary\$4 or variable or chang\$4 or first or second or plural\$4 or multiple) near2 resistiv\$5	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/21 07:41
L10	94	L8 with L9	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/21 07:41
L11	1	(L1 or L2) and L7 and L3 and L6 and L10	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/21 07:42
L12	702	chalcogenide near2 memory	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/21 07:43
L13	6	L12 and (L1 or L2)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/21 07:43
L14	1275	chalcogenide near2 (area or region or layer)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/21 07:43
L15	39	L14 and (L1 or L2)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/21 07:43
L16	23	(L1 or L2) and (L12 or L14) and carbon	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/21 07:51

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L17	6	(L1 or L2) and (L12 or L14) and carbon and resistiv\$6	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/21 07:51
L18	1198	(memory near2 cell) and (L1 or L2)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/21 07:52
L19	287	(memory near2 cell) and (L1 or L2) and resistiv\$5	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/21 07:52
L20	40	(memory near2 cell) and (L1 or L2) and resistiv\$5 and (L8 or L12 or L14)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/21 07:53
L21	23	(memory near2 cell) and (L1 or L2) and (resistiv\$5 or L3) and (L8 or L12 or L14) and carbon	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/21 07:53
L22	23	(memory near2 cell) and (L1 or L2) and (resistiv\$5 or L3) and (L8 or L12 or L14) and (carbon or L6)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/21 07:54
L23	1492	(micro near2 tip) or (micro adj tip) or ("micro-tip")	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/21 07:55
L24	158	L23.clm.	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/21 07:55
L25	5496	L3.clm.	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/21 07:55
L26	18278	L8.clm.	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/21 07:55
L27	1	((resistive near2 layer) and (active near2 layer) and ((micro near2 tip) or (micro adj tip) or ("micro-tip"))).clm.	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/21 07:56
L28	1	((resistive near2 element) and (active near2 layer) and ((micro near2 tip) or (micro adj tip) or ("micro-tip"))).clm.	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/21 07:58
L30	72	((resistive near2 (element or layer)) and substrate and (micro near2 tip) or (micro adj tip) or ("micro-tip")).clm.	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/21 07:57
L31	72	((resistive near2 (element or layer)) and substrate and (micro near2 tip) or (micro adj tip) or ("micro-tip") and resistivity).clm.	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/21 08:00
L32	1	((resistive near2 (element or layer)) and substrate and ((micro near2 tip) or (micro adj tip) or ("micro-tip")) and resistivity).clm.	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/21 08:00
S1	1	10/526391	US-PGPUB; USPAT	OR	ON	2007/02/20 11:38
S3	1	"20020006735"	US-PGPUB; USPAT	OR	ON	2007/02/20 11:54

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S5	259	"5335219" "5072116" "6757235" "5402410"	US-PGPUB; USPAT	OR	ON	2007/02/07 17:04
S6	12	((SERGE) near2 (GIDON)).INV.	US-PGPUB; USPAT	OR	ON	2007/02/20 11:24
S7	1	((YVES) near2 (SAMSON)).INV.	US-PGPUB; USPAT	OR	ON	2007/02/20 11:24
S8	1	((OLIVIER) near2 (BICHET)).INV.	US-PGPUB; USPAT	OR	ON	2007/02/20 11:24
S9	18	((BERNARD) near2 (BECHEVET)).INV.	US-PGPUB; USPAT	OR	ON	2007/02/20 11:24
S10	29	S6 or S7 or S8 or S9	US-PGPUB; USPAT	OR	ON	2007/02/20 16:41
S11	1492	(micro near2 tip) or (micro adj tip) or ("micro-tip")	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 12:13
S12	961069	probe or tip	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 11:39
S13	23787	resistiv\$5 near2 layer	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 14:54
S14	45540	(carbon or (carbon near2 resistiv\$5)) near2 (layer or element)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 11:44
S15	2822498	voltage or current	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 11:45
S16	34506	counter near2 electrode	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 11:45
S17	81078	active near2 layer	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 14:57
S18	31113	(control\$4 or vary\$4 or variable or chang\$4 or first or second or plural\$4 or multiple) near2 resistiv\$5	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 16:44
S19	72	S17 near10 S18	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 11:47
S20	94	S17 with S18	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 11:47
S21	1	(S11 or S12) same S15 same S13 same S14 same S20	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 11:48
S22	1	(S11 or S12) and S15 and S13 and S14 and S20	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/21 07:41

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S23	3	S13 same S14 same S17	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 14:57
S24	1	"20020172072"	US-PGPUB; USPAT	OR	ON	2007/02/20 11:59
S25	33150	(control\$4 or vary\$4 or variable or chang\$4 or first or second or plural\$4 or multiple or different) near2 resistiv\$5	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 14:52
S26	3153	S13 same S25	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 14:54
S27	3	S13 same S25 same S11	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 14:55
S28	72	S13 same S25 same S12	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/21 07:39
S29	24	S13 same S25 same S12 same S15	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 14:58
S30	88578	(active near2 layer) or chalcogenide	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 15:01
S31	3	S13 same S14 same S30	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 14:58
S32	702	chalcogenide near2 memory	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 15:17
S33	62	S32 and (S11 or S12)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 15:38
S34	54	S32 and (S11 or S12) and resistiv\$5	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 15:02
S35	0	S32 and S11	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/21 07:43
S36	1275	chalcogenide near2 (area or region or layer)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 15:15
S37	0	S36 and S11	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 16:49
S38	10	chalcogenide and S11	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 15:16
S39	881	chalcogenide near3 memory	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 16:44

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S40	32175	carbon near2 layer	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 15:19
S41	117	S40 and S39	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 15:20
S42	45514	carbon near2 (layer or element)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 15:20
S43	120	S42 and S39	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 15:20
S44	281	carbon near2 (layer or element) near10 resistivit\$3	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 15:23
S45	11	S44 and S39	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 15:23
S46	5618	carbon near10 resistivit\$3	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 15:23
S47	19	S46 and S39	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 15:23
S48	844	S13 with carbon	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 15:29
S49	3	(S36 or S39) and S48	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 15:28
S50	92	(S11 or S12) and (S32 or S36) and carbon	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/21 07:50
S51	56	(S11 or S12) and (S32 or S36) and carbon and resistiv\$6	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/21 07:51
S52	11	(memory near2 cell) and S11	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/21 07:52
S53	7258	(memory near2 cell) and S12	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 15:38
S54	34	"5751686" "6352753" "5353268" "5346740"	US-PGPUB; USPAT	OR	ON	2007/02/20 16:26
S55	3916	phase near2 change near2 recording	US-PGPUB; USPAT	OR	ON	2007/02/20 16:49
S56	228956	"257".clas.	US-PGPUB; USPAT	OR	ON	2007/02/20 16:27
S57	56331	"365".clas.	US-PGPUB; USPAT	OR	ON	2007/02/20 16:27

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S58	38	S55 and S56	US-PGPUB; USPAT	OR	ON	2007/02/20 16:28
S59	46	S55 and S57	US-PGPUB; USPAT	OR	ON	2007/02/20 16:33
S60	2643	S55 and "369".clas.	US-PGPUB; USPAT	OR	ON	2007/02/20 16:28
S61	5	S55 and S11	US-PGPUB; USPAT	OR	ON	2007/02/20 16:34
S62	223	S39 and S18	US-PGPUB; USPAT	OR	ON	2007/02/20 16:41
S63	38	S39 same S18	US-PGPUB; USPAT	OR	ON	2007/02/20 16:41
S64	3017	(control\$4 or vary\$4 or variable or chang\$4 or first or second or plural\$4 or multiple) near2 resistiv\$5 near2 layer	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 16:44
S65	85350	(chalcogenide or active or (phase near2 change)) near2 layer	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 16:45
S66	99	S64 same S65	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 16:45
S67	38	S64 same S65 same electrode	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 16:46
S68	1533	phase near2 change near2 memory	US-PGPUB; USPAT	OR	ON	2007/02/20 16:50
S69	9	S68 and S11	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/02/20 16:49
S70	768	(phase near2 change near2 memory) and resistiv\$6	US-PGPUB; USPAT	OR	ON	2007/02/20 16:50
S71	13	(phase near2 change near2 memory) and S44	US-PGPUB; USPAT	OR	ON	2007/02/20 16:52
S72	54	(phase near2 change near2 memory) and S64	US-PGPUB; USPAT	OR	ON	2007/02/20 16:52
S73	15	(phase near2 change near2 memory) same S64	US-PGPUB; USPAT	OR	ON	2007/02/20 16:53